

STARPOWER

SEMICONDUCTOR

IGBT

GD600HFX120C6SA

1200V/600A 2 in one-package

General Description

STARPOWER IGBT Power Module provides ultra low conduction loss as well as short circuit ruggedness.

They are designed for the applications such as general inverter and UPS.

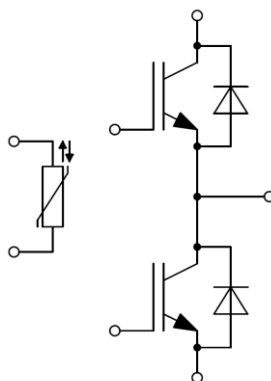
Features

- Low $V_{CE(sat)}$ Trench IGBT technology
- 10 μ s short circuit capability
- $V_{CE(sat)}$ with positive temperature coefficient
- Maximum junction temperature 175°C
- Low inductance case
- Fast & soft reverse recovery anti-parallel FWD
- Isolated copper baseplate using DBC technology

Typical Applications

- Inverter for motor drive
- AC and DC servo drive amplifier
- Uninterruptible power supply

Equivalent Circuit Schematic



Absolute Maximum Ratings $T_C=25^{\circ}\text{C}$ unless otherwise noted**IGBT**

Symbol	Description	Value	Unit
V_{CES}	Collector-Emitter Voltage	1200	V
V_{GES}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current @ $T_C=25^{\circ}\text{C}$ @ $T_C=100^{\circ}\text{C}$	1108 600	A
I_{CM}	Pulsed Collector Current $t_p=1\text{ms}$	1200	A
P_D	Maximum Power Dissipation @ $T_j=175^{\circ}\text{C}$	4054	W

Diode

Symbol	Description	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	1200	V
I_F	Diode Continuous Forward Current	600	A
I_{FM}	Diode Maximum Forward Current $t_p=1\text{ms}$	1200	A

Module

Symbol	Description	Value	Unit
T_{jmax}	Maximum Junction Temperature	175	$^{\circ}\text{C}$
T_{jop}	Operating Junction Temperature	-40 to +150	$^{\circ}\text{C}$
T_{STG}	Storage Temperature Range	-40 to +125	$^{\circ}\text{C}$
V_{ISO}	Isolation Voltage RMS, $f=50\text{Hz}$, $t=1\text{min}$	4000	V

IGBT Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C=600\text{A}, V_{GE}=15\text{V}, T_j=25^{\circ}\text{C}$		1.70	2.15	V
		$I_C=600\text{A}, V_{GE}=15\text{V}, T_j=125^{\circ}\text{C}$		1.90		
		$I_C=600\text{A}, V_{GE}=15\text{V}, T_j=150^{\circ}\text{C}$		1.95		
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=24.0\text{mA}, V_{CE}=V_{GE}, T_j=25^{\circ}\text{C}$	5.6	6.2	6.8	V
I_{CES}	Collector Cut-Off Current	$V_{CE}=V_{CES}, V_{GE}=0\text{V}, T_j=25^{\circ}\text{C}$			1.0	mA
I_{GES}	Gate-Emitter Leakage Current	$V_{GE}=V_{GES}, V_{CE}=0\text{V}, T_j=25^{\circ}\text{C}$			400	nA
R_{Gint}	Internal Gate Resistance			0.7		Ω
C_{ies}	Input Capacitance	$V_{CE}=25\text{V}, f=1\text{MHz}, V_{GE}=0\text{V}$		62.1		nF
C_{res}	Reverse Transfer Capacitance			1.74		nF
Q_G	Gate Charge	$V_{GE}=-15\dots+15\text{V}$		4.62		μC
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=600\text{A}, R_G=1.2\Omega, L_S=34\text{nH}, V_{GE}=\pm 15\text{V}, T_j=25^{\circ}\text{C}$		266		ns
t_r	Rise Time			82		ns
$t_{d(off)}$	Turn-Off Delay Time			400		ns
t_f	Fall Time			192		ns
E_{on}	Turn-On Switching Loss			65.7		mJ
E_{off}	Turn-Off Switching Loss			52.3		mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=600\text{A}, R_G=1.2\Omega, L_S=34\text{nH}, V_{GE}=\pm 15\text{V}, T_j=125^{\circ}\text{C}$		282		ns
t_r	Rise Time			94		ns
$t_{d(off)}$	Turn-Off Delay Time			448		ns
t_f	Fall Time			290		ns
E_{on}	Turn-On Switching Loss			96.2		mJ
E_{off}	Turn-Off Switching Loss			67.3		mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=600\text{A}, R_G=1.2\Omega, L_S=34\text{nH}, V_{GE}=\pm 15\text{V}, T_j=150^{\circ}\text{C}$		286		ns
t_r	Rise Time			94		ns
$t_{d(off)}$	Turn-Off Delay Time			459		ns
t_f	Fall Time			299		ns
E_{on}	Turn-On Switching Loss			107		mJ
E_{off}	Turn-Off Switching Loss			70.3		mJ
I_{SC}	SC Data	$t_p \leq 10\mu\text{s}, V_{GE}=15\text{V}, T_j=150^{\circ}\text{C}, V_{CC}=800\text{V}, V_{CEM} \leq 1200\text{V}$		2400		A

Diode Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_F	Diode Forward Voltage	$I_F=600\text{A}, V_{GE}=0\text{V}, T_j=25^{\circ}\text{C}$		1.95	2.40	V
		$I_F=600\text{A}, V_{GE}=0\text{V}, T_j=125^{\circ}\text{C}$		2.05		
		$I_F=600\text{A}, V_{GE}=0\text{V}, T_j=150^{\circ}\text{C}$		2.10		
Q_r	Recovered Charge	$V_{CC}=600\text{V}, I_F=600\text{A},$ $-di/dt=5500\text{A}/\mu\text{s}, L_s=34\text{nH},$ $V_{GE}=-15\text{V}, T_j=25^{\circ}\text{C}$		23.8		μC
I_{RM}	Peak Reverse Recovery Current			260		A
E_{rec}	Reverse Recovery Energy			11.7		mJ
Q_r	Recovered Charge	$V_{CC}=600\text{V}, I_F=600\text{A},$ $-di/dt=4700\text{A}/\mu\text{s}, L_s=34\text{nH},$ $V_{GE}=-15\text{V}, T_j=125^{\circ}\text{C}$		65.1		μC
I_{RM}	Peak Reverse Recovery Current			293		A
E_{rec}	Reverse Recovery Energy			26.4		mJ
Q_r	Recovered Charge	$V_{CC}=600\text{V}, I_F=600\text{A},$ $-di/dt=4600\text{A}/\mu\text{s}, L_s=34\text{nH},$ $V_{GE}=-15\text{V}, T_j=150^{\circ}\text{C}$		76.7		μC
I_{RM}	Peak Reverse Recovery Current			306		A
E_{rec}	Reverse Recovery Energy			30.6		mJ

NTC Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
R_{25}	Rated Resistance			5.0		k Ω
$\Delta R/R$	Deviation of R_{100}	$T_C=100^{\circ}\text{C}, R_{100}=493.3\Omega$	-5		5	%
P_{25}	Power Dissipation				20.0	mW
$B_{25/50}$	B-value	$R_2=R_{25}\exp[B_{25/50}(1/T_2-1/(298.15\text{K}))]$		3375		K
$B_{25/80}$	B-value	$R_2=R_{25}\exp[B_{25/80}(1/T_2-1/(298.15\text{K}))]$		3411		K
$B_{25/100}$	B-value	$R_2=R_{25}\exp[B_{25/100}(1/T_2-1/(298.15\text{K}))]$		3433		K

Module Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Min.	Typ.	Max.	Unit
L_{CE}	Stray Inductance		20		nH
$R_{CC'+EE'}$	Module Lead Resistance, Terminal to Chip		0.80		m Ω
R_{thJC}	Junction-to-Case (per IGBT)			0.037	K/W
	Junction-to-Case (per Diode)			0.065	
R_{thCH}	Case-to-Heatsink (per IGBT)		0.028		K/W
	Case-to-Heatsink (per Diode)		0.050		
	Case-to-Heatsink (per Module)		0.009		
M	Terminal Connection Torque, Screw M6	3.0		6.0	N.m
	Mounting Torque, Screw M5	3.0		6.0	
G	Weight of Module		350		g

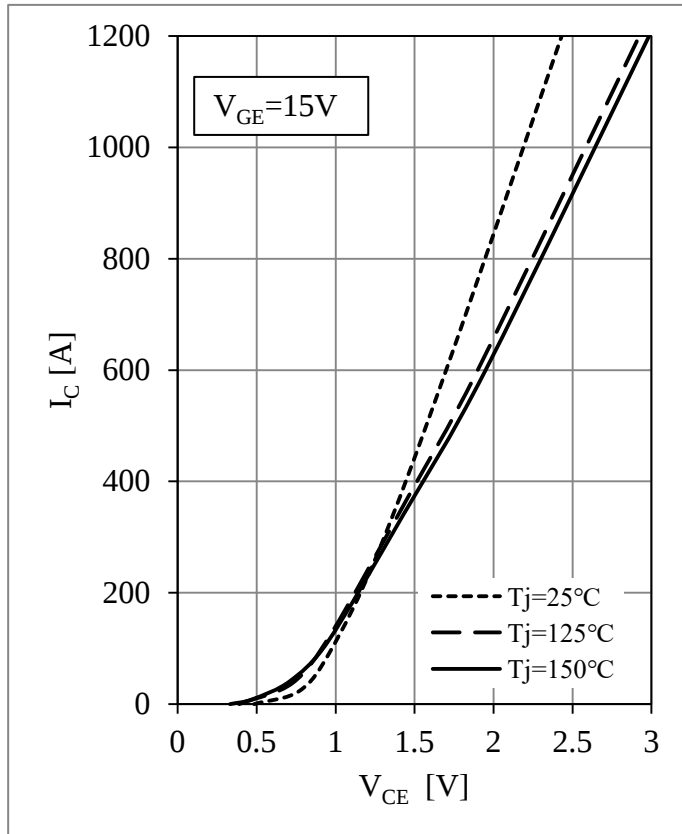


Fig 1. IGBT Output Characteristics

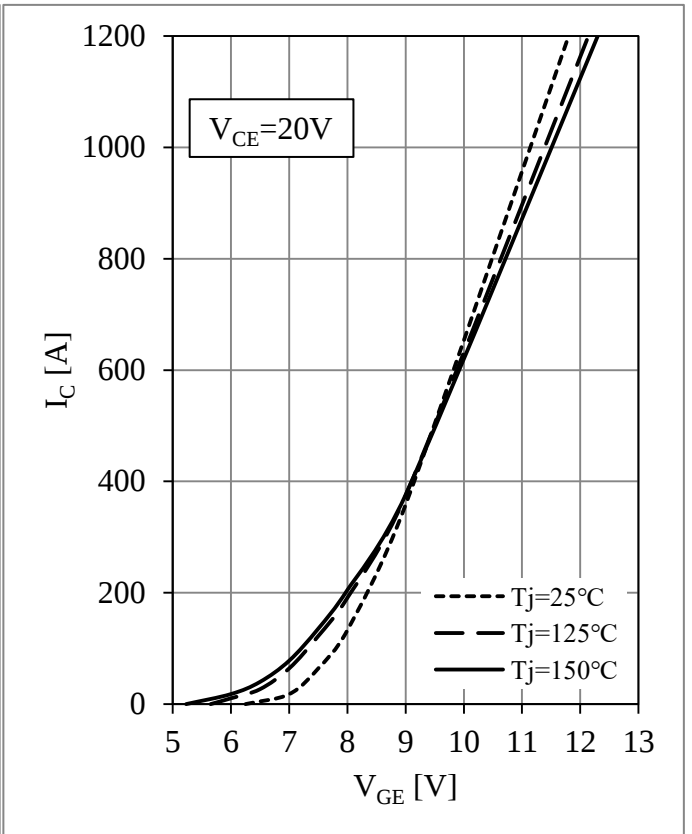
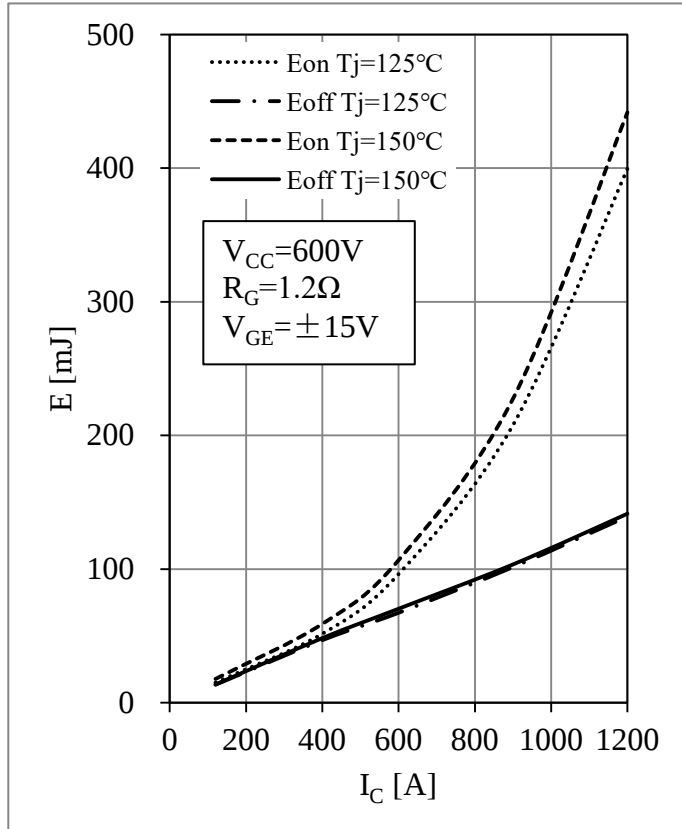
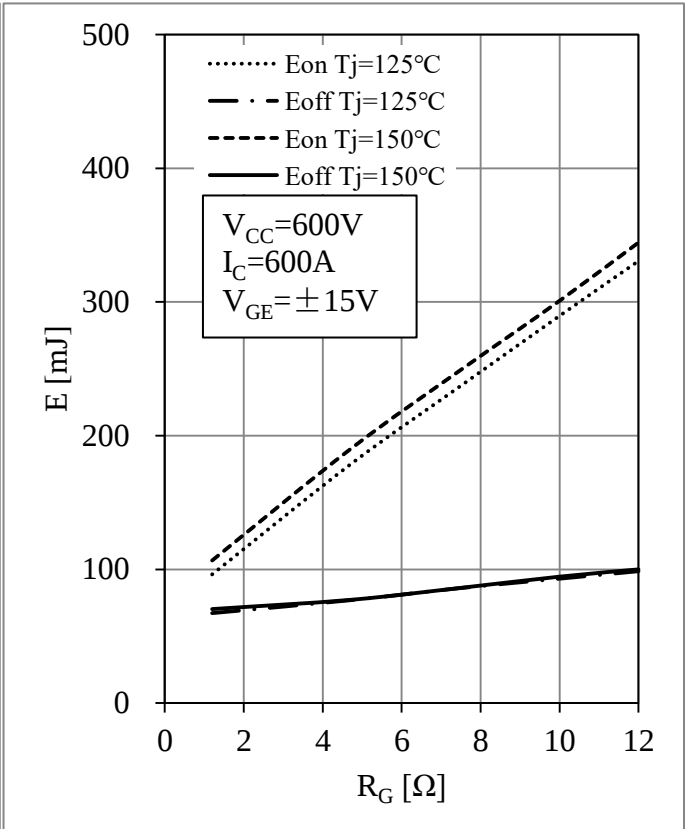


Fig 2. IGBT Transfer Characteristics

Fig 3. IGBT Switching Loss vs. I_C Fig 4. IGBT Switching Loss vs. R_G

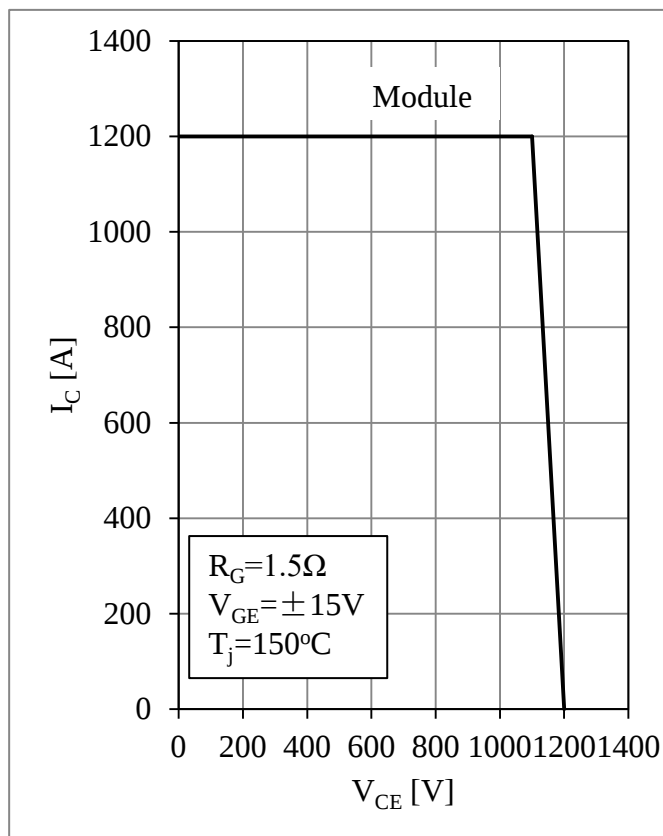


Fig 5. RBSOA

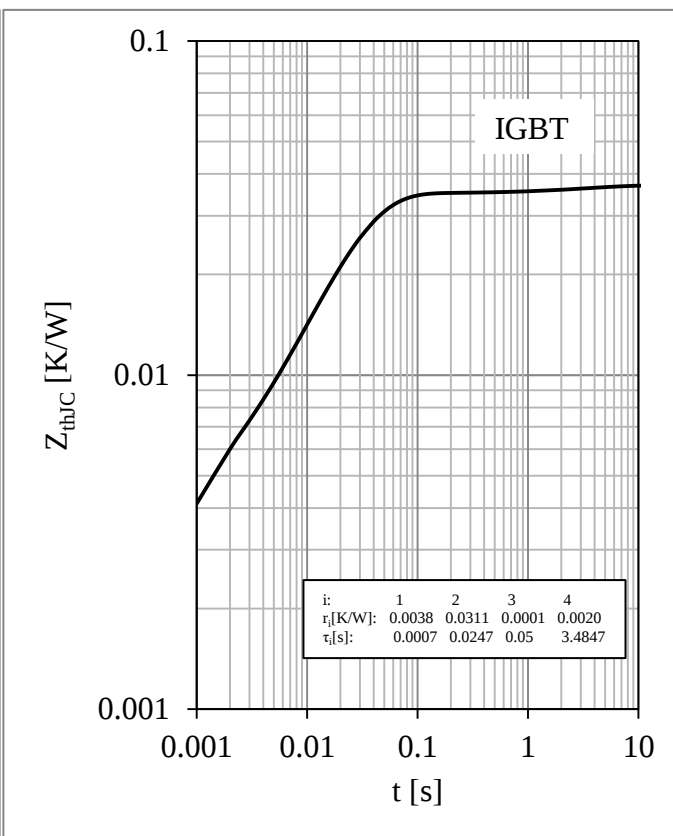


Fig 6. IGBT Transient Thermal Impedance

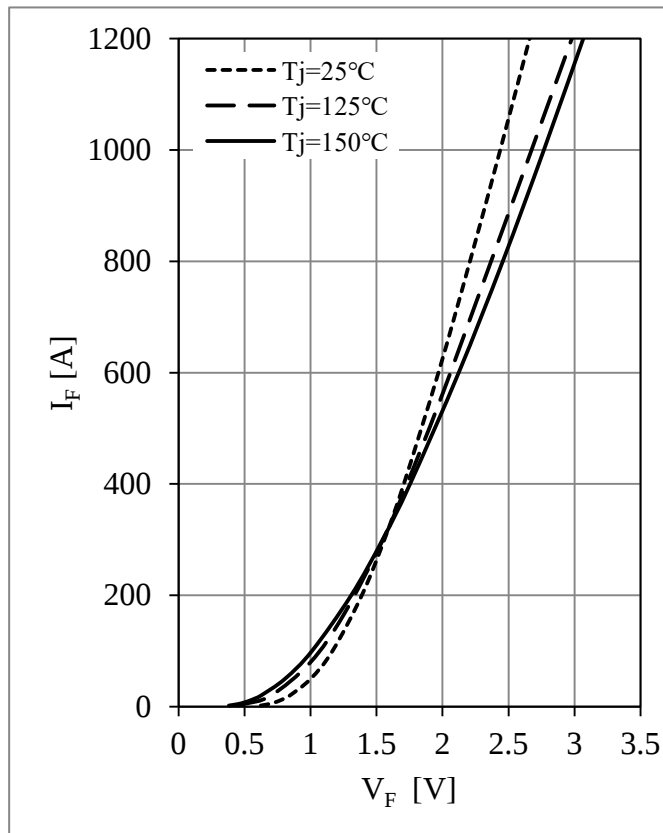
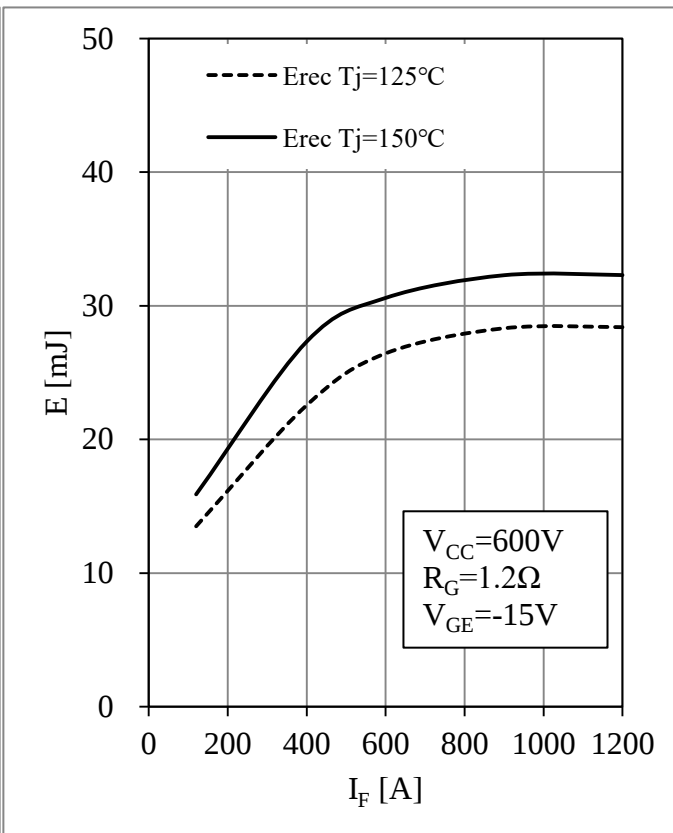
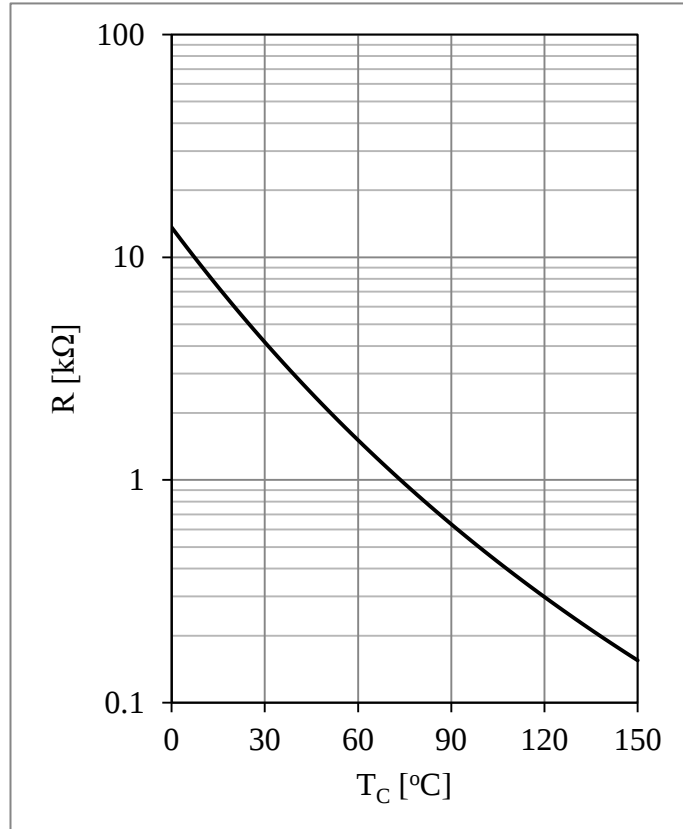
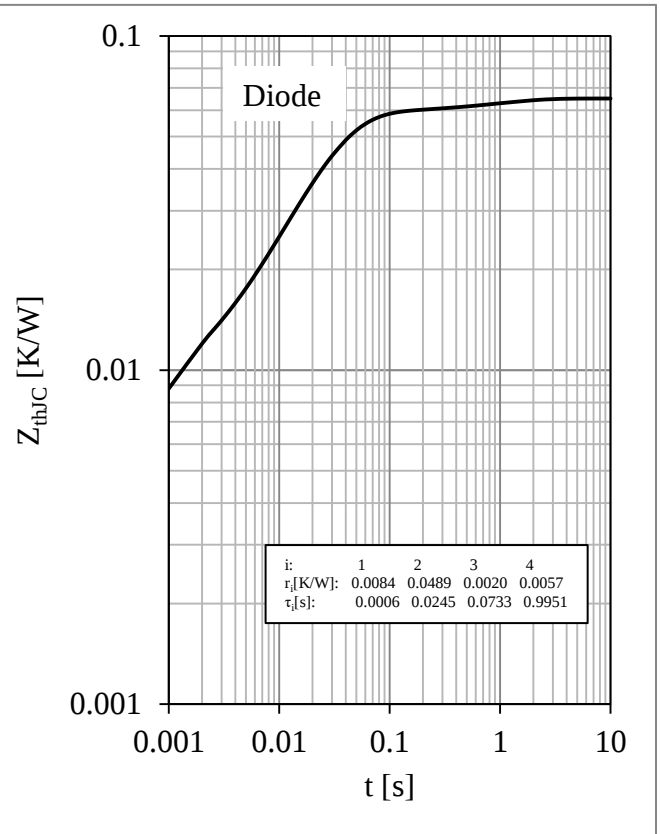
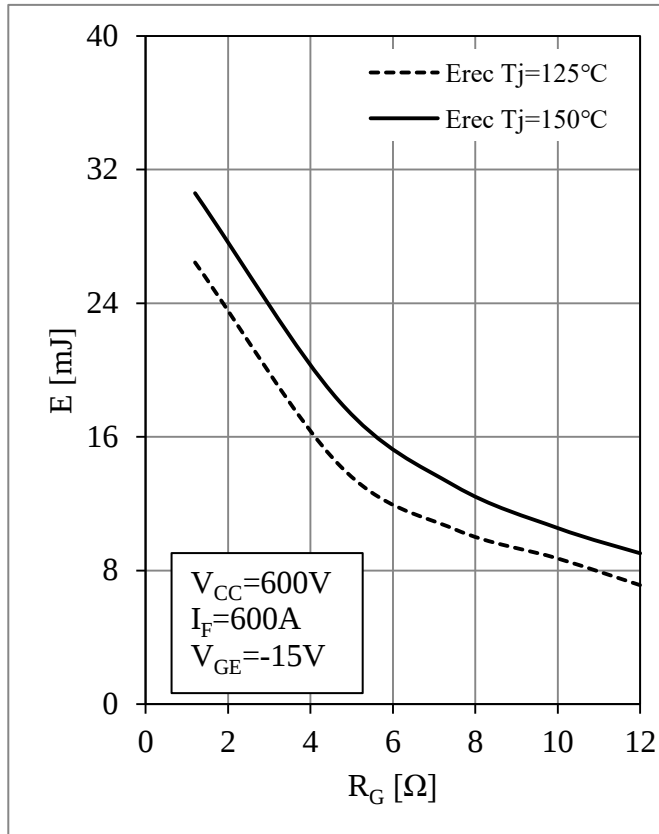
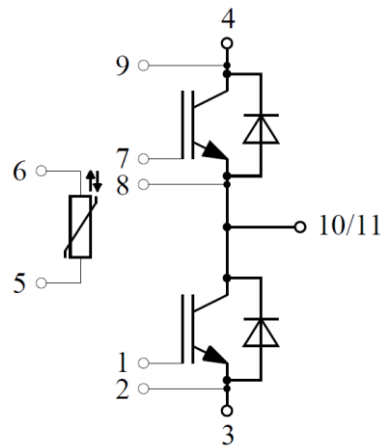


Fig 7. Diode Forward Characteristics

Fig 8. Diode Switching Loss vs. I_F

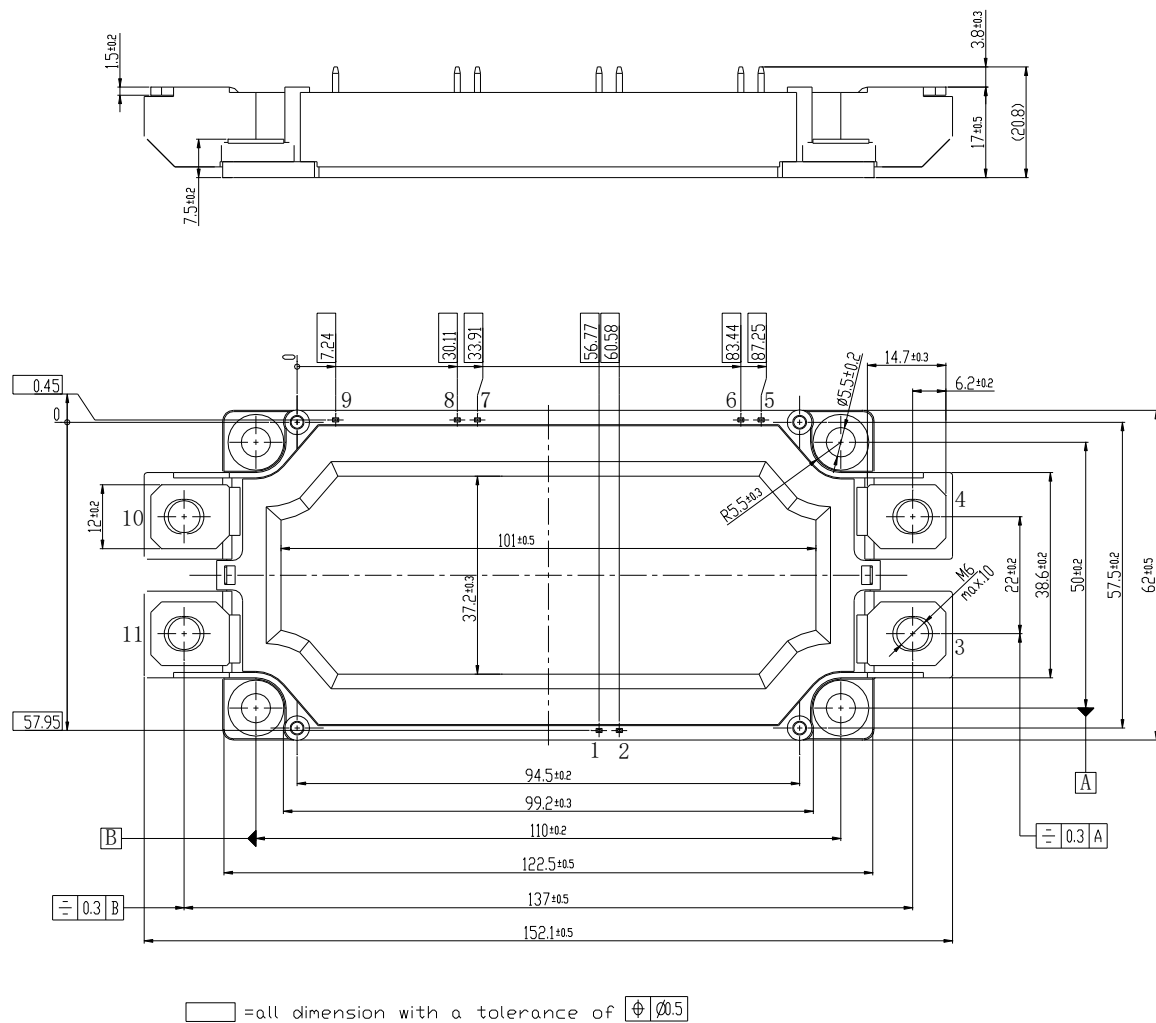


Circuit Schematic



Package Dimensions

Dimensions in Millimeters



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